BGD712C

750 MHz, 18.5 dB gain power doubler amplifier

Rev. 02 — 16 August 2007

Product data sheet

1. Product profile

1.1 General description

Hybrid high dynamic range amplifier module in SOT115J package operating at a supply voltage of 24 V (DC).

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability

1.3 Applications

■ CATV systems operating in the 40 MHz to 750 MHz frequency range.

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	f = 45 MHz	18.2	-	18.8	dB
		f = 750 MHz	19	-	20	dB
I _{tot}	total current	$V_B = 24 \text{ V}$	[1] 380	-	410	mA

^[1] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.



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2. Pinning information

Table 2: Pinning

1 input 2 common 3 common 5 +V _B 7 common 8 common		3	
2 common 3 common 5 +V _B 7 common 8 common	Pin	Description	Simplified outline Symbol
2 common 3 common 5 +V _B 7 common 8 common	1	input	
3 common 5 +V _B 7 common 8 common	2	common	13579
7 common 2 3 7 8 sym095 8 common	3	common	
7 common sym095 8 common	5	+V _B	
	7	common	
9 output	8	common	
	9	output	

3. Ordering information

Table 3: Ordering information

Type number	Package				
	Name	Description	Version		
BGD712C	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J		

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_B	supply voltage		-	30	V
Vi	input voltage		-	70	dBmV
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

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5. Characteristics

Table 5: Characteristics

Bandwidth 40 MHz to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω .

Gp	nower goin					Unit
1	power gain	f = 45 MHz	18.2	-	18.8	dB
		f = 750 MHz	19.0	-	20.0	dB
SL	slope cable equivalent	f = 45 MHz to 750 MHz	0.5	-	1.5	dB
FL	flatness of frequency response	f = 45 MHz to 100 MHz	-	-	±0.35	dB
		f = 100 MHz to 700 MHz	-	-	±0.5	dB
		f = 700 MHz to 750 MHz	-	-	±0.15	dB
S ₁₁	input return losses	f = 45 MHz to 790 MHz	17	-	-	dB
S ₂₂	output return losses	f = 45 MHz to 790 MHz	17	-	-	dB
Ψs21	phase response	f = 50 MHz	135	-	225	deg
СТВ	composite triple beat	112 channels flat; $V_o = 44 \text{ dBmV}$; measured at 745.25 MHz	-	-	-62	dB
		60 channels flat; V _o = 44 dBmV measured at 745.25 MHz	-	-67	-	dB
		79 channels flat; $V_0 = 44 \text{ dBmV}$ measured at 547.25 MHz	-	-	-68	dB
	composite second-order distortion	112 channels flat; V _o = 44 dBmV; measured at 746.5 MHz	-	-	-63	dB
		60 channels flat; $V_o = 44 \text{ dBmV}$ measured at 746.5 MHz	-	-70	-	dB
		79 channels flat; $V_o = 44 \text{ dBmV}$ measured at 548.5 MHz	-	-	-68	dB
NF	noise figure	f = 50 MHz	-	-	7	dB
		f = 750 MHz	-	-	7	dB
I _{tot}	total current		<u>[1]</u> 380	-	410	mA

^[1] The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

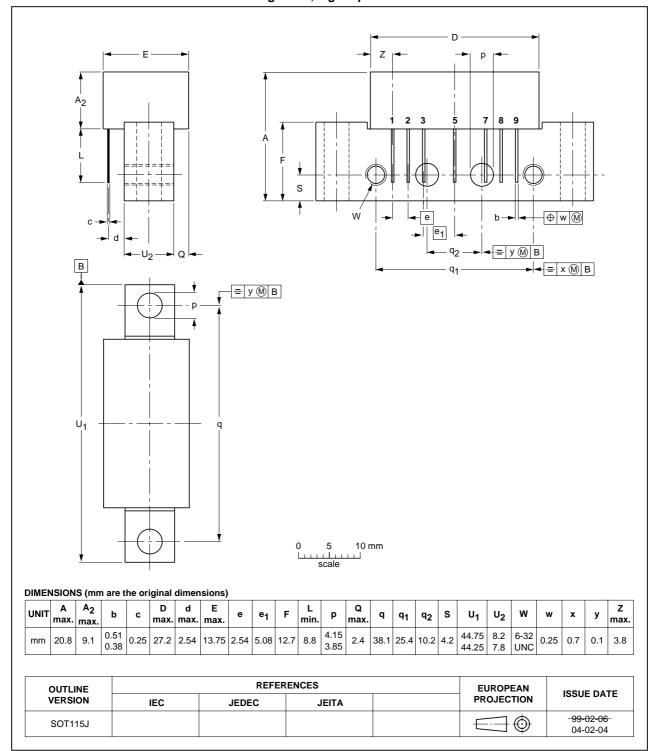


Fig 1. Package outline SOT115J

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7. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGD712C_2	20070816	Product data sheet	-	BGD712C_1
Modifications:		f this data sheet has beer NXP Semiconductors.	redesigned to comply v	with the new identity
	 Legal texts h 	ave been adapted to the r	new company name whe	ere appropriate.
	 Changed des 	scriptive title		
BGD712C_1	20060502	Product data sheet	-	-

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8. Legal information

8.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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